

•General Description

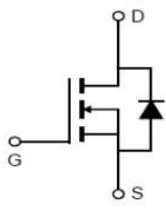
Power MOSFET LH9N50F has the low $R_{DS(on)}$, low gate charge, fast switching and excellent avalanche characteristics. This device offers extremely fast and robust body diode, and is suitable for telecom and power supplies.

•Features

- Low Thermal Resistance
- Fast Switching
- High Input Resistance

•Application

- LED/LCD/PDP TV and monitor Lighting
- Power Supplies

	$V_{DS} = 500V$ $R_{DS(ON)} = 650m\Omega$ $I_D = 9A$
 TO-220  TO-220F ■ RoHS COMPLIANT	

•Ordering Information:

Part number	LH9N50F	LH9N50F
Package	TO-220	TO-220F
Basic ordering unit (pcs)	1000	1000
Normal Package Material Ordering Code	LH9N50FT-T0220-TU	LH9N50FF-T0220F-TU
Halogen Free Ordering Code	LH9N50FT-T0220-TU-HF	LH9N50FF-T0220F-TU-HF

•Absolute Maximum Ratings (TC =25℃)

PARAMETER		SYMBOL	Value	UNIT
Drain-Source Breakdown Voltage		BV_{DSS}	500	V
Gate-Source Voltage		V_{GS}	±30	V
Continuous Drain Current	TC = 25℃	I_D	9	A
	TC = 100℃		5.4	
Pulsed drain current (TC = 25℃, tp limited by Tjmax) ¹		I_{DM}	36	A
Single Pulse Avalanche Energy ²		E_{AS}	560	mJ
Power Dissipation(TC=25℃)		P_D	38.5	W
Junction Temperature		T_J	-55~+150	℃
Storage Temperature		T_{STG}	-55~+150	℃

●Electronic Characteristics

PARAMETER	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	500	--	--	V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0	--	4.0	V
Drain-source On Resistance ³	$R_{DS(ON)}$	$V_{GS}=10V, I_D=4.5A$	--	0.65	0.85	Ω
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=500V, V_{GS}=0V, T_J=25^\circ C$	--	--	1	μA
		$V_{DS}=400V, V_{GS}=0V, T_J=125^\circ C$	--	--	100	
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 30$	--	--	± 100	nA
Forward Transconductance ³	g_{fs}	$V_{DS}=15V, I_D=4.5A$	--	8	--	S
Input Capacitance	C_{iss}	$V_{GS}=0V,$ $V_{DS}=25V$ $f=1.0MHz$	--	1050	--	pF
Output Capacitance	C_{oss}		--	95	--	
Reverse transfer Capacitance	C_{rss}		--	12	--	
Rise Time	T_r	$V_{DD}=250V,$ $R_G=25\Omega$	--	20	--	ns
Fall Time	T_f		--	18	--	
Turn-On Delay Time	$T_{d(on)}$		--	22	--	
Turn -Off Delay Time ³	$T_{d(off)}$		----	49	--	
Total Gate Charge	Q_g	$I_D=9A,$ $V_{DS}=400V$ $V_{GS}=10V$	--	21	---	nC
Gate-to-Source Charge	Q_{gs}		--	4.8	--	
Gate-to-Drain Charge	Q_{gd}		--	7.6	---	
Continuous Diode Forward Current	I_S		--	--	9	A
Diode Forward Voltage	V_{SD}	$T_J=25^\circ C, I_S=9A$ $V_{GS}=0V$	--	--	1.4	V
Reverse Recovery Time	t_{rr}	$I_f=I_S$ $di_F/dt=100A/\mu s$ 3	--	380	--	ns
Reverse Recovery Charge	Q_{rr}		--	1.9	--	μC

●Thermal Characteristics

PARAMETER	SYMBOL	MAX	UNIT
Thermal Resistance Junction-case	R_{thJC}	3.25	$^\circ C/W$
Thermal Resistance Junction-ambient	R_{thJA}	62.5	$^\circ C/W$

Notes:

1.Repetitive Rating: Pulse width limited by maximum junction temperature.

2. $I_{AS}=9A, V_{DD}=50V, R_G=25\Omega, L=14mH$, Starting $T_J=25^\circ C$

3. Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$

• **Typical Characteristics**

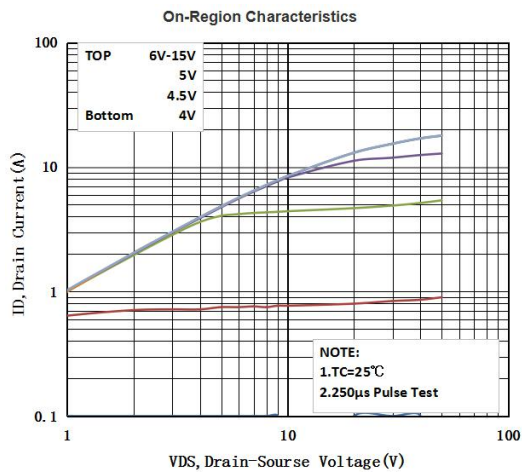


Fig1 Typical Output Characteristics, $T_C=25^{\circ}\text{C}$

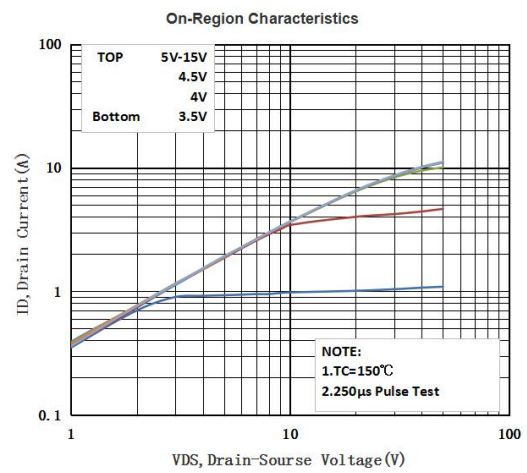


Fig2 Typical Output Characteristics, $T_C=150^{\circ}\text{C}$

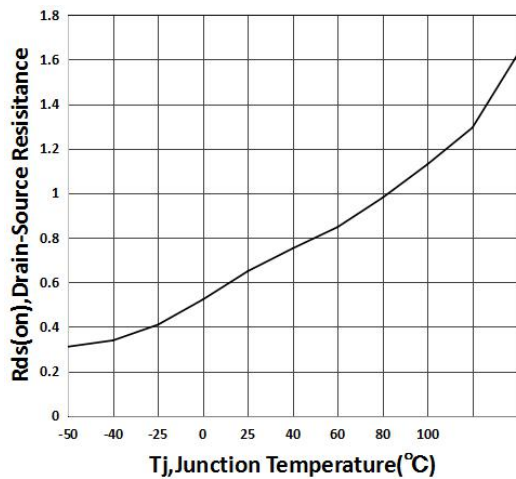


Fig3 Resistance Vs. Temperature

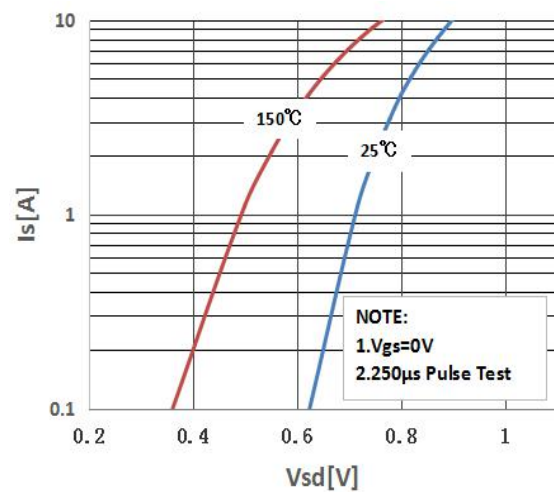


Fig4 Typical Source-Drain Diode Forward Voltage

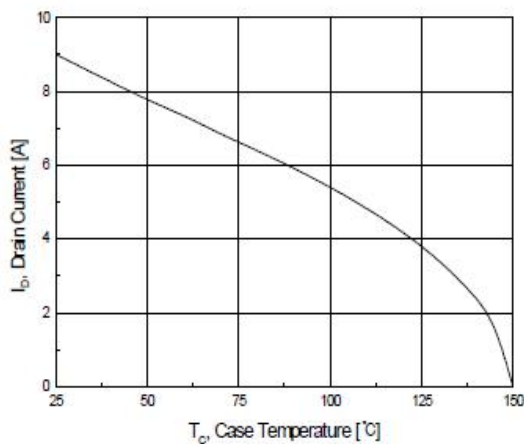


Fig5 Maximum Drain Current Vs. Case Temperature

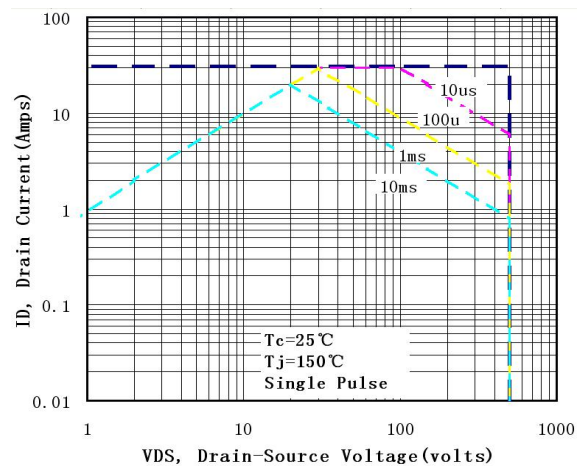
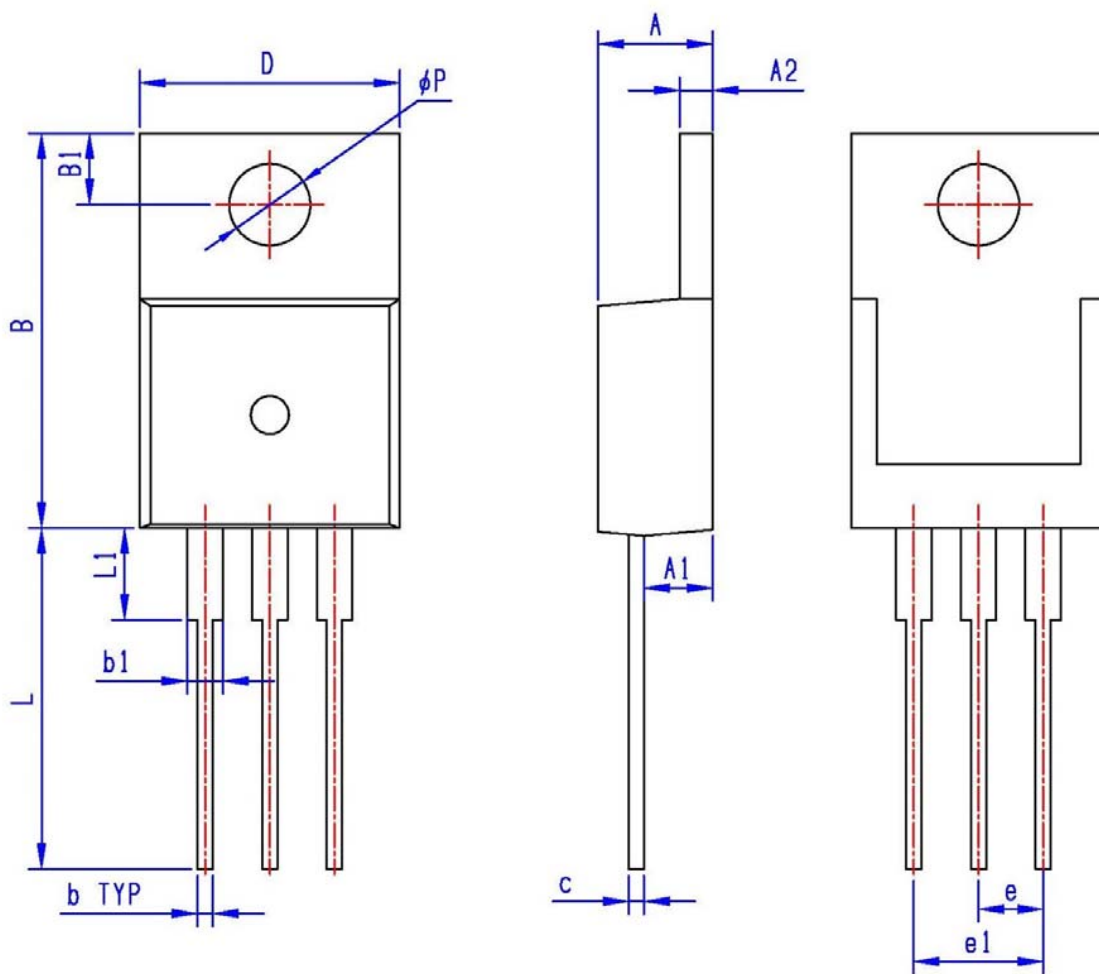


Fig6 Maximum Safe Operating Area

•Dimensions (TO-220)

UNIT:mm

SYMBOL	min	max	SYMBOL	min	max
A	4.25	4.85	B1	2.60	3.00
A1	2.30	3.00	e	2.40	2.70
A2	1.20	1.40	e1	4.95	5.25
b	0.60	0.90	L	12.60	14.40
b1	1.10	1.70	L1	2.40	4.00
c	0.40	0.70	∅P	3.50	3.90
D	9.80	10.60			
B	15.20	16.20			



●Dimensions (TO-220F)

UNIT:mm

SYMBOL	min	max	SYMBOL	min	max
A	4.20	4.80	E1	8.30	8.70
A1	2.50	2.90	e	2.40	2.70
A2	2.90	3.30	e1	4.95	5.25
b	0.40	0.80	F	2.50	2.90
b1	1.10	1.50	L	13.00	14.00
c	0.50	0.70	L1	3.00	4.00
D	9.80	10.60	∅P	2.90	3.50
E	14.60	15.60			

